

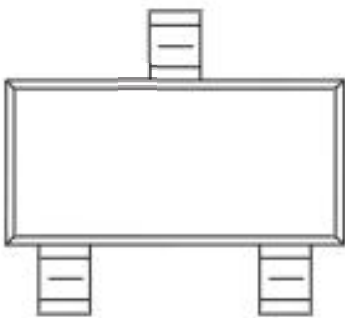


SHENZHEN MENGKE ELECTRONICS TECHNOLOGY CO.,LTD

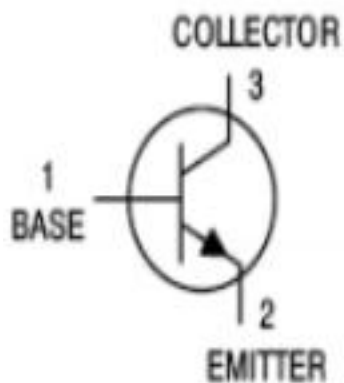
## SOT-23 Plastic-Encapsulate Transistors

### 2SC2712 TRANSISTOR (NPN)

#### MARKING:

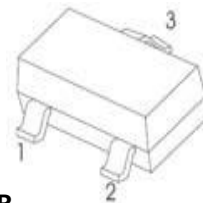


#### Equivalent Circuit:



#### SOT-23

- 1.BASE
- 2.EMITTER
- 3.COLLECTOR



#### FEATURES:

- Complimentary to 2SA1162
- LOW noise NF= 1DB(Typ) 10dB (MAX)

#### MAXIMUM RATINGS (Ta=25 unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	50	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	150	mA
Collector Power Dissipation	PC	150	mW
Thermal Resistance From Junction To Ambient	ROJA	833	/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 +150	°C



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### ELECTRICAL CHARACTERISTICS (Ta=25 unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	60			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	50			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA, IC=0	5			V
Collector cut-off current	ICBO	VCB=60 V , IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 5V , IC=0			0.1	μA
DC current gain	hFE	VCE=6V, IC= 2mA	70		700	
Collector-emitter saturation voltage	VCE(sat)	IC=100 mA, IB= 10mA		0.1	0.25	V
Base-emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1	V
Transition frequency	fT	VCE=10V, IC= 1mA f=1MHz	80			MHz
Collector Output Capacitance	Cob	VCE=10V, IE= 0 f=1MHz		2.0	3.5	pf
Noise Figure	NF	VCE=6V, IC= 0.1mA Rg=10kΩ; f=1KHz		1.0	10	dB

### CLASSIFICATION OF hFE

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700
Marking	LO	LY	LG	LL



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

